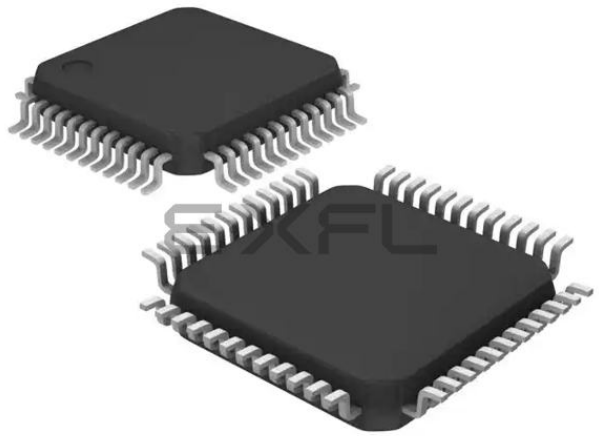

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	STM8A
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	38
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 10x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 150°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8af6248tdx

Contents

3 Product line-up

Table 1. STM8AF6246/48/66/68 product line-up

Order code	Package	Medium density Flash program memory (byte)	RAM (byte)	Data EE (byte)	10-bit A/D ch.	Timers (IC/OC/PWM)	Serial interfaces	I/0 wakeup pins
STM8AF/P6268	LQFP48 (7x7)	32 K	2 K	1 K	10	1x8-bit: TIM4 3x16-bit: TIM1, TIM2, TIM3 (9/9/9)	LIN(UART), SPI, I²C	38/35
STM8AF/P6248		16 K		0.5 K				
STM8AF/P6266	LQFP32 (7x7)	32 K		1 K	7	1x8-bit: TIM4 3x16-bit: TIM1, TIM2, TIM3 (8/8/8)	LIN(UART), SPI, I²C	25/23
STM8AF/P6246		16 K		0.5 K				
STM8AF/P6266	VFQFPN32	32 K		1 K	7	1x8-bit: TIM4 3x16-bit: TIM1, TIM2, TIM3 (8/8/8)	LIN(UART), SPI, I²C	25/23
STM8AF/P6246		16 K		0.5 K				

UART mode

- Full duplex, asynchronous communications - NRZ standard format (mark/space)
- High-precision baud rate generator
  - A common programmable transmit and receive baud rates up to $f_{MASTER}/16$
- Programmable data word length (8 or 9 bits) – 1 or 2 stop bits – parity control
- Separate enable bits for transmitter and receiver
- Error detection flags
- Reduced power consumption mode
- Multi-processor communication - enter mute mode if address match does not occur
- Wakeup from mute mode (by idle line detection or address mark detection)
- Two receiver wakeup modes:
  - Address bit (MSB)
  - Idle line

5.10 Input/output specifications

The product features four different I/O types:

- Standard I/O 2 MHz
- Fast I/O up to 10 MHz
- High sink 8 mA, 2 MHz
- True open drain (I^2C interface)

To decrease EMI (electromagnetic interference), high sink I/Os have a limited maximum slew rate. The rise and fall times are similar to those of standard I/Os.

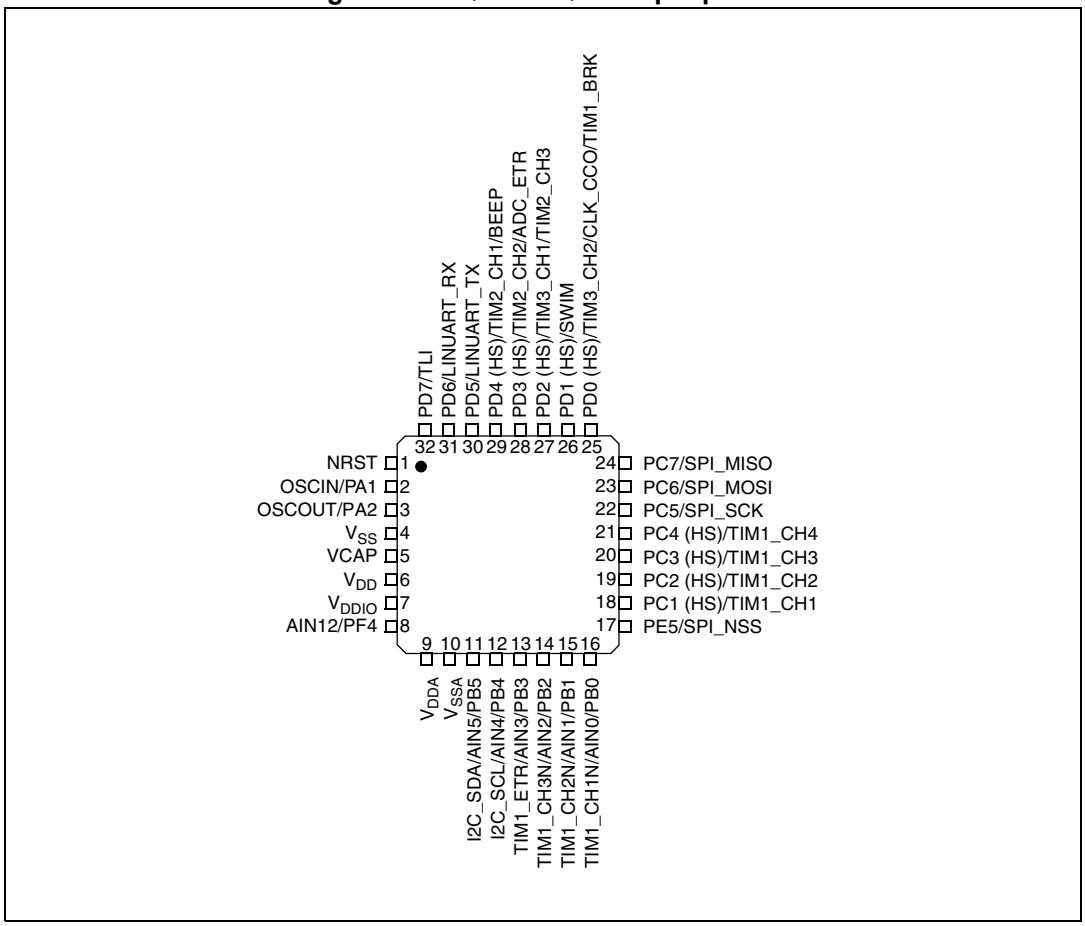
The analog inputs are equipped with a low leakage analog switch. Additionally, the schmitt-trigger input stage on the analog I/Os can be disabled in order to reduce the device standby consumption.

STM8A I/Os are designed to withstand current injection. For a negative injection current of 4 mA, the resulting leakage current in the adjacent input does not exceed 1 µA. Thanks to this feature, external protection diodes against current injection are no longer required.

6 Pinouts and pin description

6.1 Package pinouts

Figure 3. VFQFPN/LQFP 32-pin pinout



1. (HS) high sink capability.

Table 8. STM8AF6246/48/66/68 (32 Kbyte) microcontroller pin description(1)(2) (continued)

Pin number		Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
LQFP48	VFQFPN/LQFP32			floating	wpu	Ext. interrupt	High sink	Speed	OD	PP			
24		PE6/AIN9	I/O	**X**	X	X	-	O1	X	X	**Port E7**	Analog input 9	-
25	17	PE5/SPI_NSS	I/O	**X**	X	X	-	O1	X	X	**Port E5**	SPI master/slave select	-
26	18	PC1/TIM1_CH1	I/O	**X**	X	X	HS	O3	X	X	**Port C1**	Timer 1 - channel 1	-
27	19	PC2/TIM1_CH2	I/O	**X**	X	X	HS	O3	X	X	**Port C2**	Timer 1- channel 2	-
28	20	PC3/TIM1_CH3	I/O	**X**	X	X	HS	O3	X	X	**Port C3**	Timer 1 - channel 3	-
29	21	PC4/TIM1_CH4	I/O	**X**	X	X	HS	O3	X	X	**Port C4**	Timer 1 - channel 4	-
30	22	PC5/SPI_SCK	I/O	**X**	X	X		O3	X	X	**Port C5**	SPI clock	-
31	-	V_{SSIO_2}	S	-	-	-	-	-	-	-	I/O ground		-
32	-	V_{DDIO_2}	S	-	-	-	-	-	-	-	I/O power supply		-
33	23	PC6/SPI_MOSI	I/O	**X**	X	X	-	O3	X	X	**Port C6**	SPI master out/ slave in	-
34	24	PC7/SPI_MISO	I/O	**X**	X	X	-	O3	X	X	**Port C7**	SPI master in/ slave out	-
35	-	PG0	I/O	**X**	X	-	-	O1	X	X	**Port G0**	-	-
36	-	PG1	I/O	**X**	X	-	-	O1	X	X	**Port G1**	-	-
37	-	PE3/TIM1_BKIN	I/O	**X**	X	X	-	O1	X	X	**Port E3**	Timer 1 - break input	-
38	-	PE2/I^2C_SDA	I/O	**X**	-	X	-	O1	T(6)	-	**Port E2**	I^2C data	-
39	-	PE1/I^2C_SCL	I/O	**X**	-	X	-	O1	T(6)	-	**Port E1**	I^2C clock	-
40	-	PE0/CLK_CCO	I/O	**X**	X	X	-	O3	X	X	**Port E0**	Configurable clock output	-
41	25	PD0/TIM3_CH2	I/O	**X**	X	X	HS	O3	X	X	**Port D0**	Timer 3 - channel 2	TIM1_BKIN [AFR3]/ CLK_CCO [AFR2]
42	26	PD1/SWIM(7)	I/O	X	**X**	X	HS	O4	X	X	**Port D1**	SWIM data interface	-
43	27	PD2/TIM3_CH1	I/O	**X**	X	X	HS	O3	X	X	**Port D2**	Timer 3 - channel 1	TIM2_CH3 [AFR1]
44	28	PD3/TIM2_CH2	I/O	**X**	X	X	HS	O3	X	X	**Port D3**	Timer 2 - channel 2	ADC_ETR [AFR0]
45	29	PD4/TIM2_CH1/ BEEP	I/O	**X**	X	X	HS	O3	X	X	**Port D4**	Timer 2 - channel 1	BEEP output [AFR7]
46	30	PD5/ LINUART_TX	I/O	**X**	X	X	-	O1	X	X	**Port D5**	LINUART data transmit	-

Table 11. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 50F3	BEEP	BEEP_CSR	BEEP control/status register	0x1F
0x00 50F4 to 0x00 50FF	Reserved area (12 bytes)			
0x00 5200	SPI	SPI_CR1	SPI control register 1	0x00
0x00 5201		SPI_CR2	SPI control register 2	0x00
0x00 5202		SPI_ICR	SPI interrupt control register	0x00
0x00 5203		SPI_SR	SPI status register	0x02
0x00 5204		SPI_DR	SPI data register	0x00
0x00 5205		SPI_CRCPR	SPI CRC polynomial register	0x07
0x00 5206		SPI_RXCRCR	SPI Rx CRC register	0xFF
0x00 5207		SPI_TXCRCR	SPI Tx CRC register	0xFF
0x00 5208 to 0x00 520F	Reserved area (8 bytes)			
0x00 5210	I2C	I2C_CR1	I2C control register 1	0x00
0x00 5211		I2C_CR2	I2C control register 2	0x00
0x00 5212		I2C_FREQR	I2C frequency register	0x00
0x00 5213		I2C_OARL	I2C own address register low	0x00
0x00 5214		I2C_OARH	I2C own address register high	0x00
0x00 5215		Reserved area (1 byte)		
0x00 5216		I2C_DR	I2C data register	0x00
0x00 5217		I2C_SR1	I2C status register 1	0x00
0x00 5218		I2C_SR2	I2C status register 2	0x00
0x00 5219		I2C_SR3	I2C status register 3	0x00
0x00 521A		I2C_ITR	I2C interrupt control register	0x00
0x00 521B		I2C_CCRL	I2C clock control register low	0x00
0x00 521C		I2C_CCRH	I2C clock control register high	0x00
0x00 521D		I2C_TRISER	I2C TRISE register	0x02
0x00 521E to 0x00 523F	Reserved area (24 bytes)			

Table 11. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5265	TIM1	TIM1_CCR1H	TIM1 capture/compare register 1 high	0x00
0x00 5266		TIM1_CCR1L	TIM1 capture/compare register 1 low	0x00
0x00 5267		TIM1_CCR2H	TIM1 capture/compare register 2 high	0x00
0x00 5268		TIM1_CCR2L	TIM1 capture/compare register 2 low	0x00
0x00 5269		TIM1_CCR3H	TIM1 capture/compare register 3 high	0x00
0x00 526A		TIM1_CCR3L	TIM1 capture/compare register 3 low	0x00
0x00 526B		TIM1_CCR4H	TIM1 capture/compare register 4 high	0x00
0x00 526C		TIM1_CCR4L	TIM1 capture/compare register 4 low	0x00
0x00 526D		TIM1_BKR	TIM1 break register	0x00
0x00 526E		TIM1_DTR	TIM1 dead-time register	0x00
0x00 526F		TIM1_OISR	TIM1 output idle state register	0x00
0x00 5270 to 0x00 52FF	Reserved area (147 bytes)			
0x00 5300	TIM2	TIM2_CR1	TIM2 control register 1	0x00
0x00 5301		TIM2_IER	TIM2 interrupt enable register	0x00
0x00 5302		TIM2_SR1	TIM2 status register 1	0x00
0x00 5303		TIM2_SR2	TIM2 status register 2	0x00
0x00 5304		TIM2_EGR	TIM2 event generation register	0x00
0x00 5305		TIM2_CCMR1	TIM2 capture/compare mode register 1	0x00
0x00 5306		TIM2_CCMR2	TIM2 capture/compare mode register 2	0x00
0x00 5307		TIM2_CCMR3	TIM2 capture/compare mode register 3	0x00
0x00 5308		TIM2_CCER1	TIM2 capture/compare enable register 1	0x00
0x00 5309		TIM2_CCER2	TIM2 capture/compare enable register 2	0x00
0x00 530A		TIM2_CNTRH	TIM2 counter high	0x00
0x00 530B		TIM2_CNTRL	TIM2 counter low	0x00
00 530C0x		TIM2_PSCR	TIM2 prescaler register	0x00
0x00 530D		TIM2_ARRH	TIM2 auto-reload register high	0xFF
0x00 530E		TIM2_ARRL	TIM2 auto-reload register low	0xFF
0x00 530F		TIM2_CCR1H	TIM2 capture/compare register 1 high	0x00
0x00 5310		TIM2_CCR1L	TIM2 capture/compare register 1 low	0x00
0x00 5311		TIM2_CCR2H	TIM2 capture/compare reg. 2 high	0x00
0x00 5312		TIM2_CCR2L	TIM2 capture/compare register 2 low	0x00
0x00 5313		TIM2_CCR3H	TIM2 capture/compare register 3 high	0x00

8 Interrupt table

Table 14. STM8A interrupt table

Priority	Source block	Description	Interrupt vector address	Wakeup from Halt	Comments
-	Reset	Reset	0x00 8000	Yes	User RESET vector
-	TRAP	SW interrupt	0x00 8004	-	-
0	TLI	External top level interrupt	0x00 8008	-	-
1	AWU	Auto-wakeup from Halt	0x00 800C	Yes	-
2	Clock controller	Main clock controller	0x00 8010	-	-
3	MISC	Ext interrupt E0	0x00 8014	Yes	Port A interrupts
4	MISC	Ext interrupt E1	0x00 8018	Yes	Port B interrupts
5	MISC	Ext interrupt E2	0x00 801C	Yes	Port C interrupts
6	MISC	Ext interrupt E3	0x00 8020	Yes	Port D interrupts
7	MISC	Ext interrupt E4	0x00 8024	Yes	Port E interrupts
8	Reserved(1)	-	-	-	-
9	Reserved(1)	-	-	-	-
10	SPI	End of transfer	0x00 8030	Yes	-
11	Timer 1	Update/overflow/ trigger/break	0x00 8034	-	-
12	Timer 1	Capture/compare	0x00 8038	-	-
13	Timer 2	Update/overflow	0x00 803C	-	-
14	Timer 2	Capture/compare	0x00 8040	-	-
15	Timer 3	Update/overflow	0x00 8044	-	-
16	Timer 3	Capture/compare	0x00 8048	-	-
17	Reserved(1)	-	-	-	-
18	Reserved(1)	-	-	-	-
19	I^2C	I^2C interrupts	0x00 8054	Yes	-
20	LINUART	Tx complete/error	0x00 8058	-	-
21	LINUART	Receive data full reg.	0x00 805C	-	-
22	ADC	End of conversion	0x00 8060	-	-
23	Timer 4	Update/overflow	0x00 8064	-	-
24	EEPROM	End of Programming/ Write in not allowed area	0x00 8068	-	-

1. All reserved and unused interrupts must be initialized with ‘IRET’ for robust programming.

Table 16. Option byte description (continued)

Option byte no.	Description
OPT3	**HSITRIM: Trimming option for 16 MHz internal RC oscillator** 0: 3-bit on-the-fly trimming (compatible with devices based on the 128K silicon) 1: 4-bit on-the-fly trimming
	LSI_EN: Low speed internal clock enable 0: LSI clock is not available as CPU clock source 1: LSI clock is available as CPU clock source
	IWDG_HW: Independent watchdog 0: IWDG independent watchdog activated by software 1: IWDG independent watchdog activated by hardware
	WWDG_HW: Window watchdog activation 0: WWDG window watchdog activated by software 1: WWDG window watchdog activated by hardware
	WWDG_HALT: Window watchdog reset on Halt 0: No reset generated on Halt if WWDG active 1: Reset generated on Halt if WWDG active
OPT4	**EXTCLK: External clock selection** 0: External crystal connected to OSCIN/OSCOUT 1: External clock signal on OSCIN
	CKAWUSEL: Auto-wakeup unit/clock 0: LSI clock source selected for AWU 1: HSE clock with prescaler selected as clock source for AWU
	PRSC[1:0]: AWU clock prescaler 00: Reserved 01: 16 MHz to 128 kHz prescaler 10: 8 MHz to 128 kHz prescaler 11: 4 MHz to 128 kHz prescaler
OPT5	**HSECNT[7:0]: HSE crystal oscillator stabilization time** This configures the stabilization time to 0.5, 8, 128, and 2048 HSE cycles with corresponding option byte values of 0xE1, 0xD2, 0xB4, and 0x00.
OPT6	**TMU**[3:0]: Enable temporary memory unprotection 0101: TMU disabled (permanent ROP). Any other value: TMU enabled.
OPT7	**Reserved**
OPT8	**TMU_KEY 1 [7:0]: Temporary unprotection key 0** Temporary unprotection key: Must be different from 0x00 or 0xFF
OPT9	**TMU_KEY 2 [7:0]: Temporary unprotection key 1** Temporary unprotection key: Must be different from 0x00 or 0xFF
OPT10	**TMU_KEY 3 [7:0]: Temporary unprotection key 2** Temporary unprotection key: Must be different from 0x00 or 0xFF
OPT11	**TMU_KEY 4 [7:0]: Temporary unprotection key 3** Temporary unprotection key: Must be different from 0x00 or 0xFF

10 Electrical characteristics

10.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS}.

10.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = -40 °C, T_A = 25 °C, and T_A = T_{Amax} (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production.

10.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 5.0 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range.

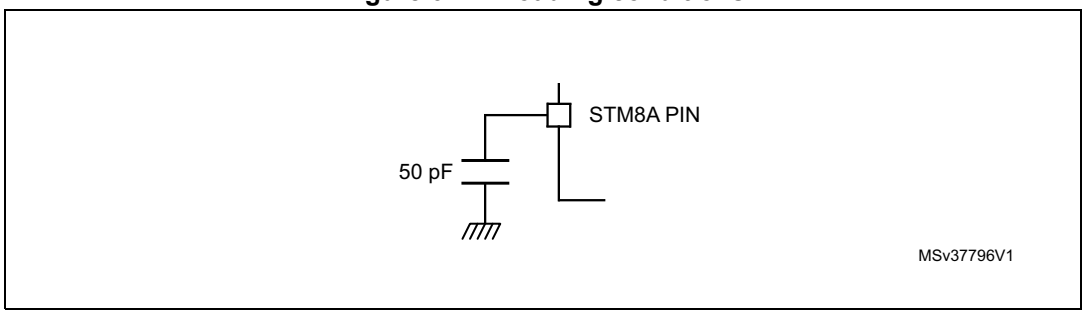
10.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

10.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

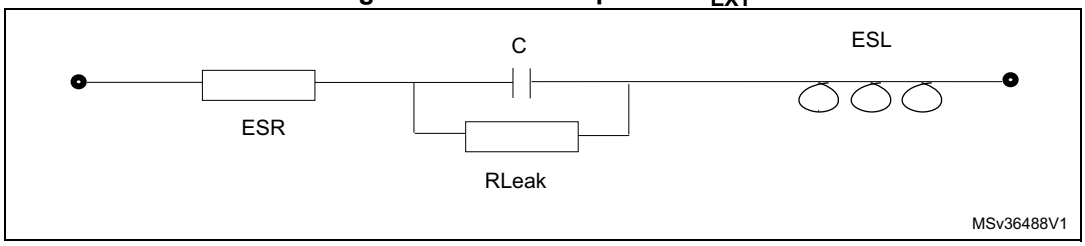
Figure 6. Pin loading conditions



10.3.1 VCAP external capacitor

Stabilization for the main regulator is achieved connecting an external capacitor C_{EXT} to the V_{CAP} pin. C_{EXT} is specified in *Table 21*. Care should be taken to limit the series inductance to less than 15 nH.

Figure 9. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance and ESL is the equivalent inductance.

10.3.2 Supply current characteristics

The current consumption is measured as described in *Figure 6 on page 49* and *Figure 7 on page 50*.

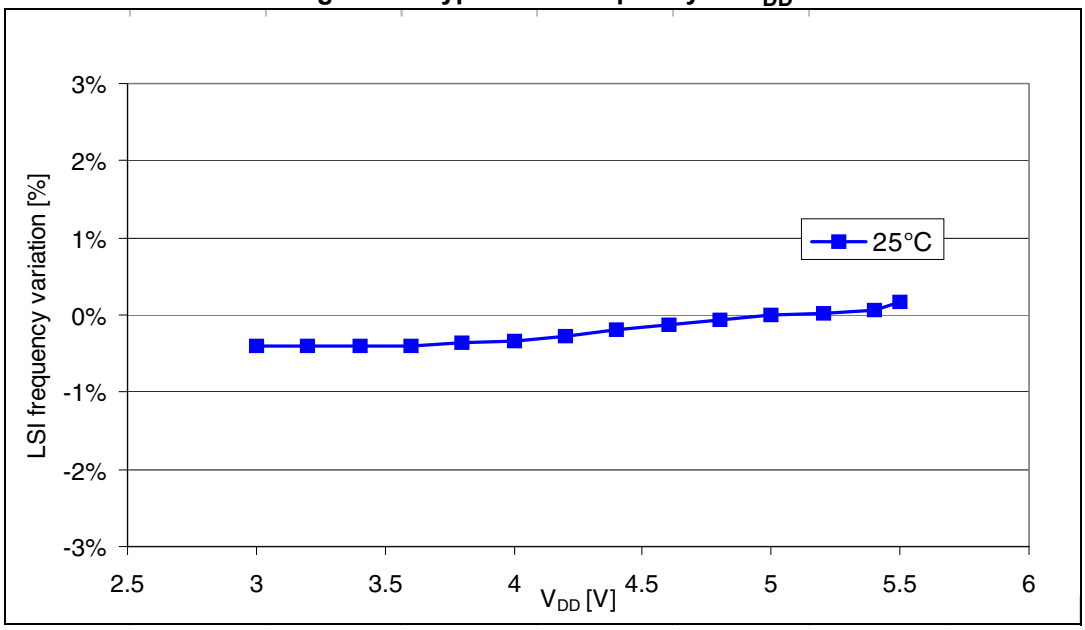
If not explicitly stated, general conditions of temperature and voltage apply.

Table 23. Total current consumption in Run, Wait and Slow mode. General conditions for V_{DD} apply, T_A = -40 to 150 °C

Symbol	Parameter	Conditions		Typ	Max	Unit
$I_{DD(RUN)}$(1)	Supply current in Run mode	All peripherals clocked, code executed from Flash program memory, HSE external clock (without resonator)	f_{CPU} = 16 MHz	7.4	14	mA
			f_{CPU} = 8 MHz	4.0	7.4(2)	
			f_{CPU} = 4 MHz	2.4	4.1(2)	
			f_{CPU} = 2 MHz	1.5	2.5	
$I_{DD(RUN)}$(1)	Supply current in Run mode	All peripherals clocked, code executed from RAM and EEPROM, HSE external clock (without resonator)	f_{CPU} = 16 MHz	3.7	5.0	
			f_{CPU} = 8 MHz	2.2	3.0(2)	
			f_{CPU} = 4 MHz	1.4	2.0(2)	
			f_{CPU} = 2 MHz	1.0	1.5	
$I_{DD(WFI)}$(1)	Supply current in Wait mode	CPU stopped, all peripherals off, HSE external clock	f_{CPU} = 16 MHz	1.65	2.5	
			f_{CPU} = 8 MHz	1.15	1.9(2)	
			f_{CPU} = 4 MHz	0.90	1.6(2)	
			f_{CPU} = 2 MHz	0.80	1.5	
$I_{DD(SLOW)}$(1)	Supply current in Slow mode	f_{CPU} scaled down, all peripherals off, code executed from RAM	Ext. clock 16 MHz f_{CPU} = 125 kHz	1.50	1.95	
			LSI internal RC f_{CPU} = 128 kHz	1.50	1.80(2)	

1. The current due to I/O utilization is not taken into account in these values.
2. Values not tested in production. Design guidelines only.

Figure 19. Typical LSI frequency vs V_{DD}



10.3.5 Memory characteristics

Flash program memory/data EEPROM memory

General conditions: T_A = -40 to 150 °C.

Table 32. Flash program memory/data EEPROM memory

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	Operating voltage (all modes, execution/write/erase)	f_{CPU} is 0 to 16 MHz with 0 ws	3.0	-	5.5	V
V_{DD}	Operating voltage (code execution)	f_{CPU} is 0 to 16 MHz with 0 ws	2.6	-	5.5	
t_{prog}	Standard programming time (including erase) for byte/word/block (1 byte/4 bytes/128 bytes)	-	-	6	6.6	ms
	Fast programming time for 1 block (128 bytes)	-	-	3	3.3	
t_{erase}	Erase time for 1 block (128 bytes)	-	-	3	3.3	

Table 33. Flash program memory

Symbol	Parameter	Condition	Min	Max	Unit
T_{WE}	Temperature for writing and erasing	-	-40	150	°C
N_{WE}	Flash program memory endurance (erase/write cycles)(1)	T_A = 25 °C	1000	-	cycles
t_{RET}	Data retention time	T_A = 25 °C	40	-	years
		T_A = 55 °C	20	-	

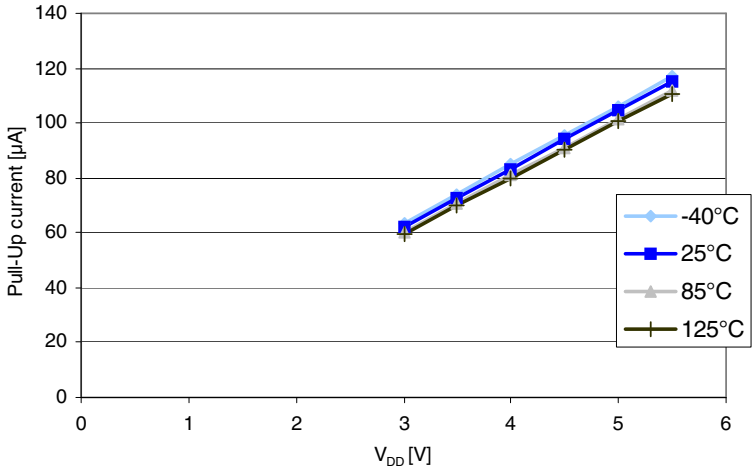
1. The physical granularity of the memory is four bytes, so cycling is performed on four bytes even when a write/erase operation addresses a single byte.

Table 34. Data memory

Symbol	Parameter	Condition	Min	Max	Unit
T_{WE}	Temperature for writing and erasing	-	-40	150	°C
N_{WE}	Data memory endurance(1) (erase/write cycles)	T_A = 25 °C	300 k	-	cycles
		T_A = -40°C to 125 °C	100 k(2)	-	
t_{RET}	Data retention time	T_A = 25 °C	40(2)(3)	-	years
		T_A = 55 °C	20(2)(3)	-	

1. The physical granularity of the memory is four bytes, so cycling is performed on four bytes even when a write/erase operation addresses a single byte.
2. More information on the relationship between data retention time and number of write/erase cycles is available in a separate technical document.
3. Retention time for 256B of data memory after up to 1000 cycles at 125 °C.

Figure 22. Typical pull-up current I_{pu} vs V_{DD} @ four temperatures



Note: The pull-up is a pure resistor (slope goes through 0).

Typical output level curves

Figure 23 to *Figure 32* show typical output level curves measured with output on a single pin.

Figure 23. Typ. V_{OL} @ V_{DD} = 3.3 V (standard ports)

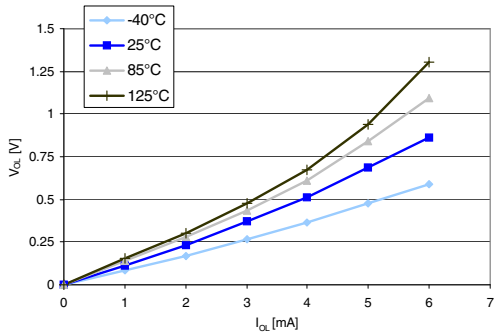


Figure 24. Typ. V_{OL} @ V_{DD} = 5.0 V (standard ports)

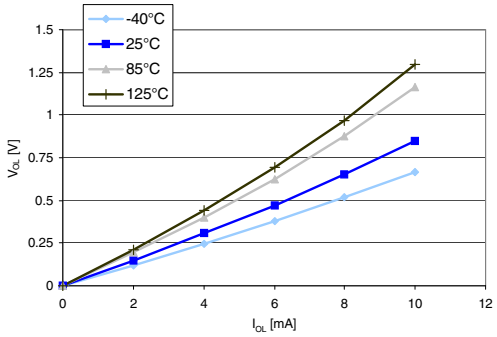


Figure 25. Typ. V_{OL} @ V_{DD} = 3.3 V (true open drain ports)

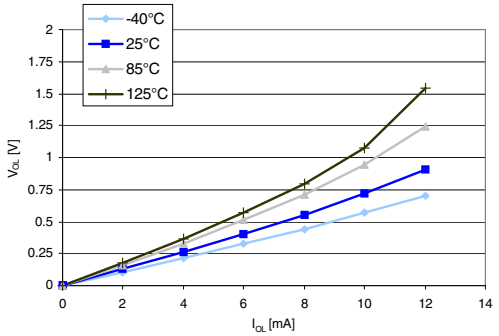


Figure 26. Typ. V_{OL} @ V_{DD} = 5.0 V (true open drain ports)

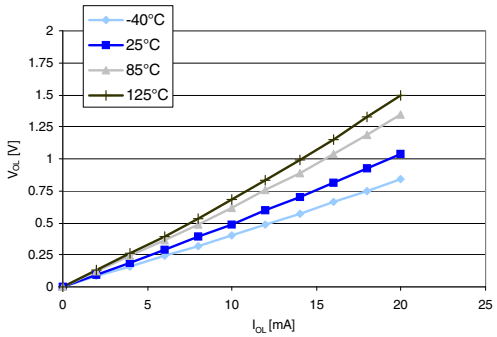


Figure 27. Typ. V_{OL} @ V_{DD} = 3.3 V (high sink ports)

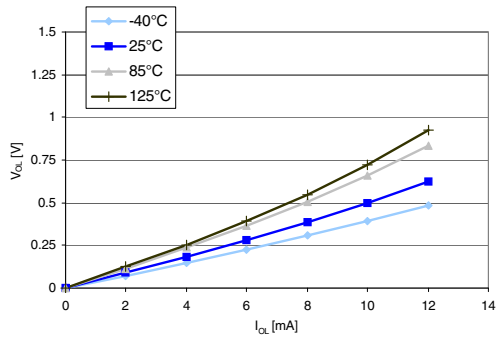


Figure 28. Typ. V_{OL} @ V_{DD} = 5.0 V (high sink ports)

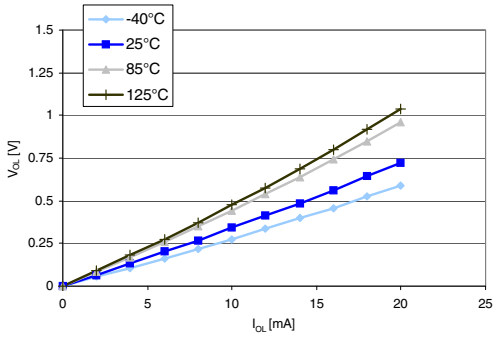


Figure 29. Typ. V_{DD} - V_{OH} @ V_{DD} = 3.3 V (standard ports)

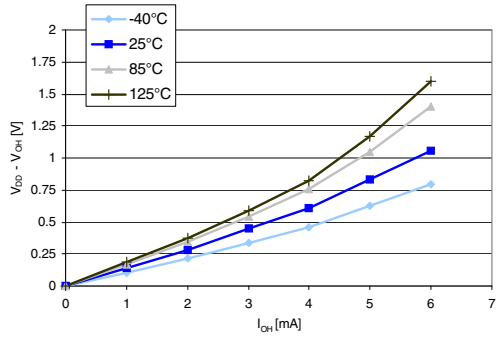


Figure 30. Typ. V_{DD} - V_{OH} @ V_{DD} = 5.0 V (standard ports)

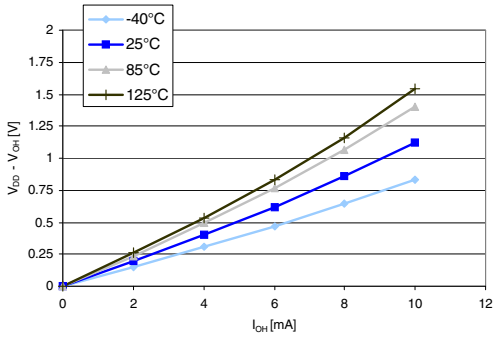


Figure 31. Typ. V_{DD} - V_{OH} @ V_{DD} = 3.3 V (high sink ports)

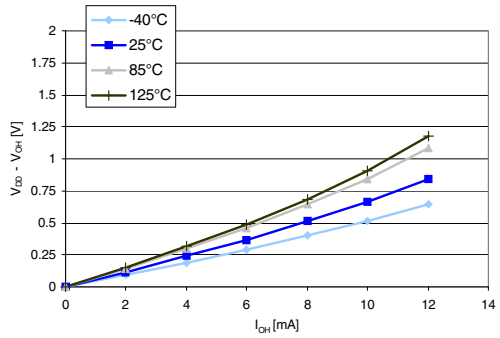
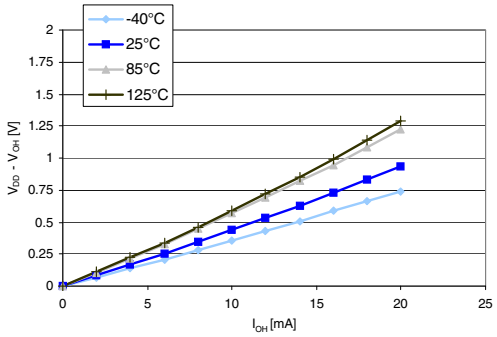
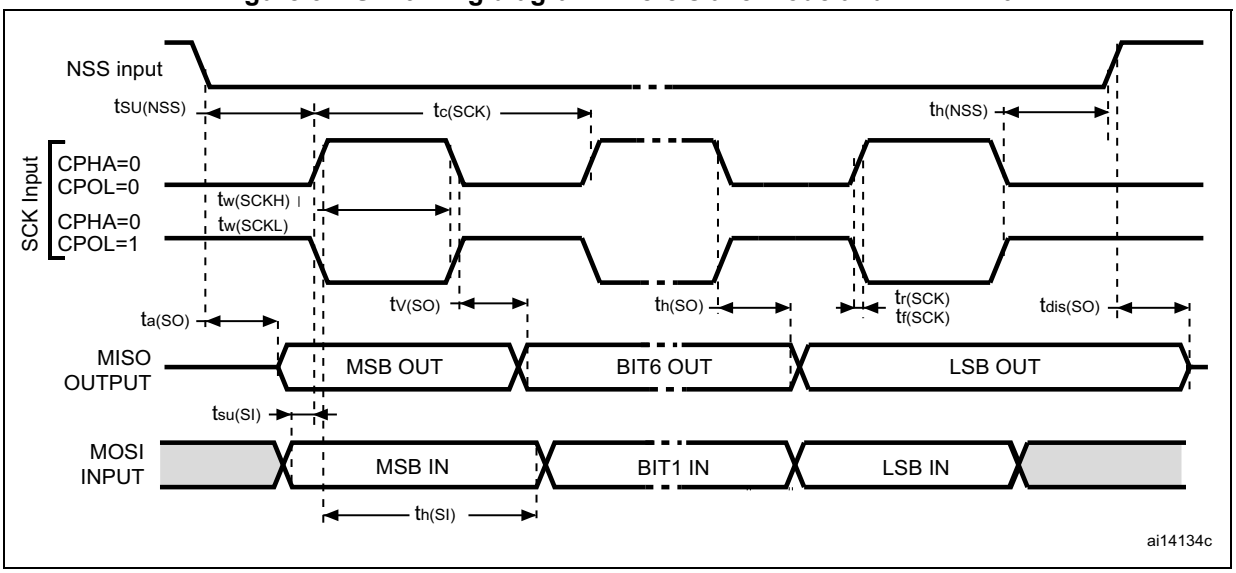


Figure 32. Typ. V_{DD} - V_{OH} @ V_{DD} = 5.0 V (high sink ports)



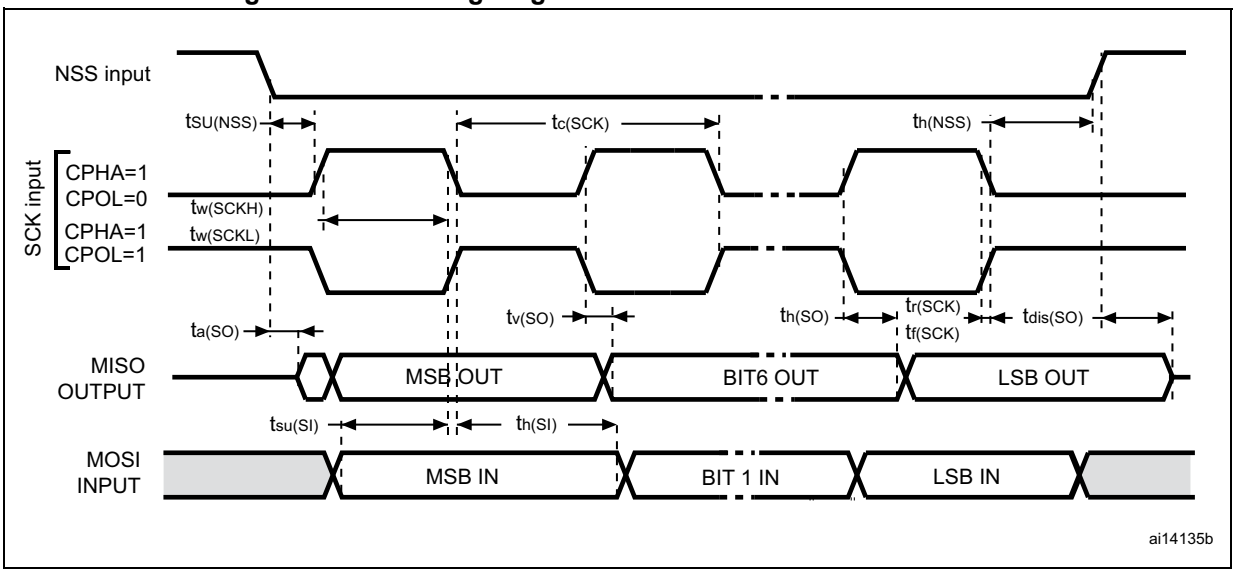
3. Values based on design simulation and/or characterization results, and not tested in production.
4. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
5. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.

Figure 37. SPI timing diagram where slave mode and CPHA = 0



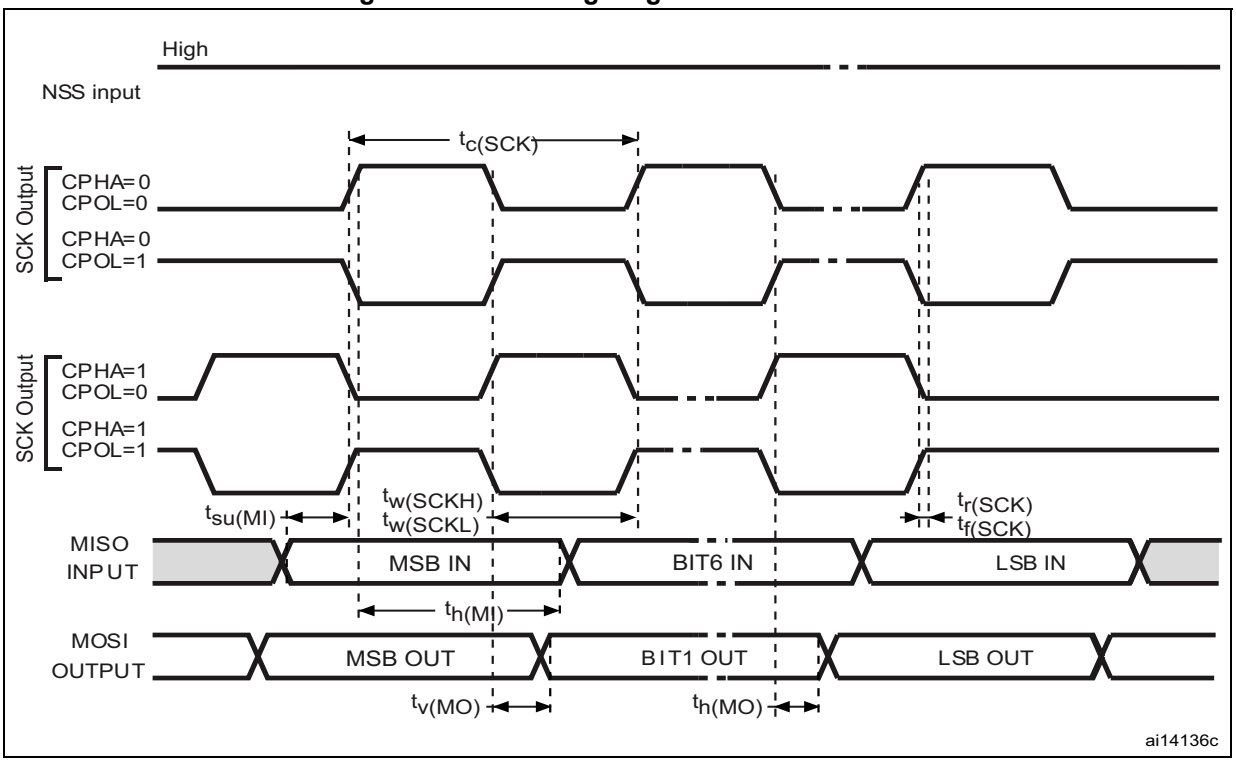
1. Measurement points are at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

Figure 38. SPI timing diagram where slave mode and CPHA = 1



1. Measurement points are at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

Figure 39. SPI timing diagram - master mode



1. Measurement points are at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

Electromagnetic interference (EMI)

Emission tests conform to the IEC 61967-2 standard for test software, board layout and pin loading.

Table 43. EMI data

Symbol	Parameter	Conditions				Unit
		General conditions	Monitored frequency band	Max f_{CPU}(1)		
				8 MHz	16 MHz	
S_{EMI}	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP80 package conforming to IEC 61967-2	0.1 MHz to 30 MHz	15	17	dBµV
			30 MHz to 130 MHz	18	22	
			130 MHz to 1 GHz	-1	3	
	EMI level		-	2	2.5	

1. Data based on characterization results, not tested in production.

Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (3 positive then 3 negative pulses separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). This test conforms to the JESD22-A114A/A115A standard. For more details, refer to the application note AN1181.

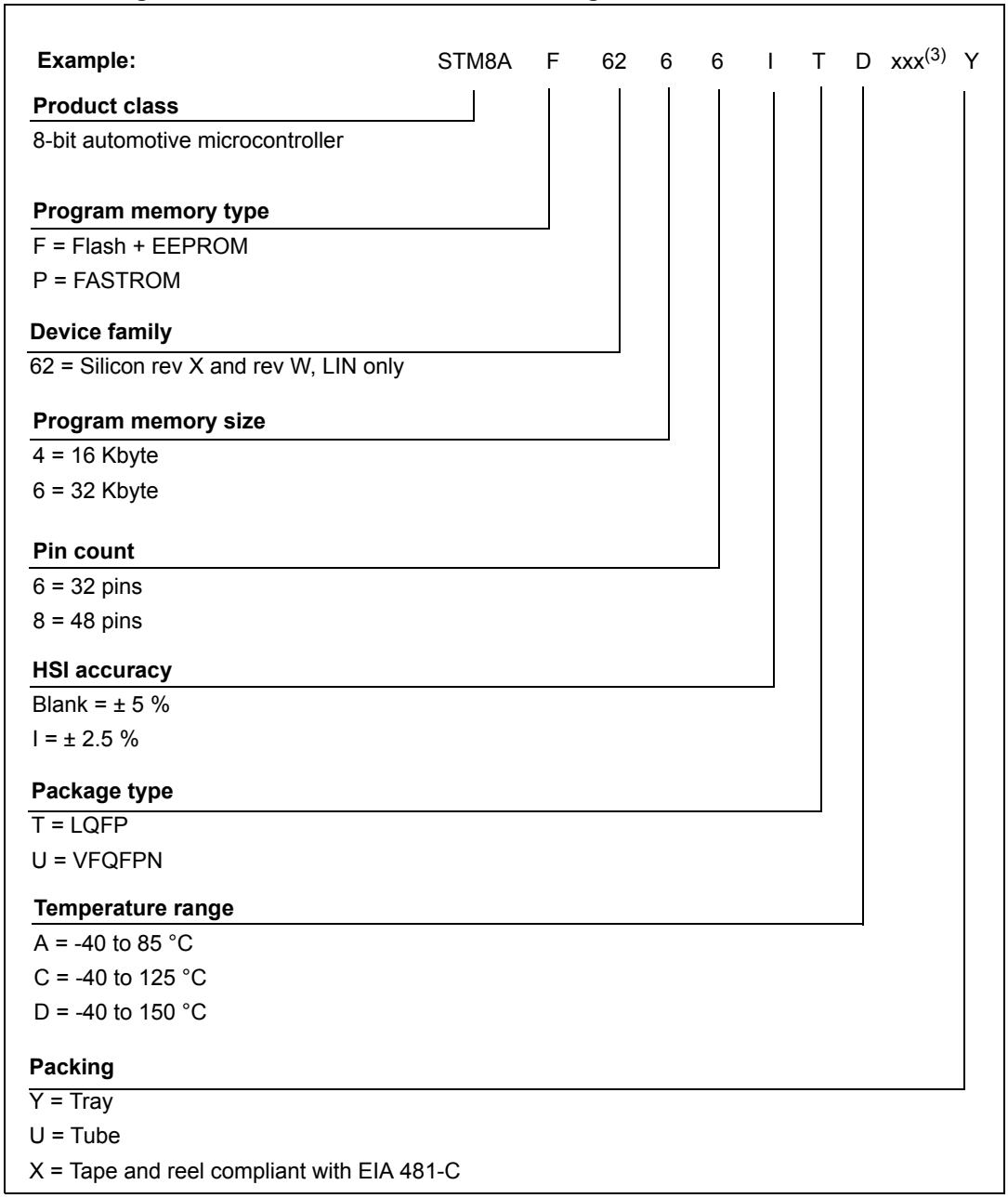
Table 44. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human body model)	T_A = 25°C, conforming to JESD22-A114	3A	4000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charge device model)	T_A= 25°C, conforming to JESD22-C101	3	500	
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine model)	T_A= 25°C, conforming to JESD22-A115	B	200	

1. Data based on characterization results, not tested in production

12 Ordering information

Figure 51. STM8AF6246/48/66/68 ordering information scheme(1) (2)



1. For a list of available options (e.g. memory size, package) and orderable part numbers or for further information on any aspect of this device, please go to *www.st.com* or contact the nearest ST Sales Office.
2. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.
3. Customer specific FASTROM code or custom device configuration. This field shows ‘SSS’ if the device contains a super set silicon, usually equipped with bigger memory and more I/Os. This silicon is supposed to be replaced later by the target silicon.

Table 50. Document revision history (continued)

Date	Revision	Changes
31-Jan-2011	5	Modified references to reference manual, and Flash programming manual in the whole document. Added reference to AEC Q100 standard on cover page. Renamed timer types as follows: – Auto-reload timer to general purpose timer – Multipurpose timer to advanced control timer – System timer to basic timer Introduced concept of medium density Flash program memory. Updated timer names in *Figure: STM8A block diagram.* Added TMU brief description in *Section: Flash program and data EEPROM*, and updated TMU_MAXATT description in *Table: Option byte description*. Updated clock sources in clock controller features. Changed 16MHZTRIM0 to HSITRIM bit in *Section: User trimming.* Added *Table: Peripheral clock gating bits.* Updated *Section: Low-power operating modes.* Added calibration using TIM3 in *Section: Auto-wakeup counter.* Added *Table: ADC naming* and *Table: Communication peripheral naming correspondence.* Added *Note 1* related AIN12 pin in *Section: Analog-to-digital converter (ADC)* and *Table: STM8AF61xx/62xx (32 Kbyte) microcontroller pin description.* Updated SPI data rate to 10 Mbit/s or $f_{MASTER}/2$ in *Section: Serial peripheral interface (SPI).* Added reset state in *Table: Legend/abbreviation.* *Table: STM8AF61xx/62xx (32 Kbyte) microcontroller pin description:* added *Note 7* related to PD1/SWIM, modified *Note 6,* corrected wpu input for PE1 and PE2, and renamed TIMn_CCx and TIMn_NCCx to TIMn_CHx and TIMn_CHxN, respectively. ***Section: Register map:*** Replaced tables describing register maps and reset values for non-volatile memory, global configuration, reset status, clock controller, interrupt controller, timers, communication interfaces, and ADC, by *Table: General hardware register map*. Added *Note 1* for Px_IDR registers in *Table: I/O port hardware register map.* Updated register reset values for Px_IDR registers. Added SWIM and debug module register map.